

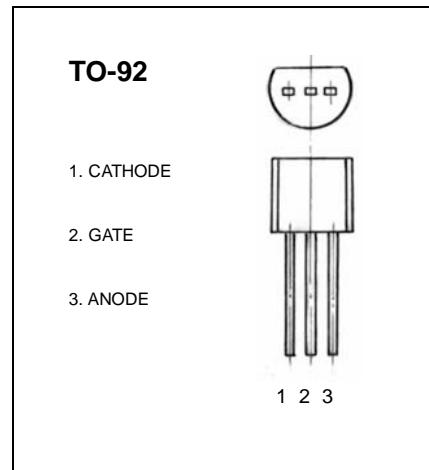


JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

PCR 0.6 A Silicon Planar pnpn Thyristor

FEATURES

Current- I_{GT} : 120 μ A I_{TRMS} : 0.6 A V_{DRM} : 400 V

Operating and storage junction temperature range

 T_J, T_{stg} : -55°C to +150°C

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

| Parameter | Symbol | Test conditions | MIN | MAX | UNIT |
|-----------------------------------|-----------|--------------------------|-----|-----|---------|
| On state voltage | V_{TM} | $I_{TM}=0.6A$ | | 1.7 | V |
| Gate trigger voltage | V_{GTF} | $V_{AK}=7V$ | | 0.8 | V |
| Repetitive peak off-state voltage | V_{DRM} | $I_{DRM}= 10\mu A$ | 400 | | V |
| Holding current | I_H | $I_{HL}= 20mA, Av = 7 V$ | | 5 | mA |
| Gate trigger current | I_{GTF} | A2 | 5 | 15 | μA |
| | | A1 | 15 | 30 | μA |
| | | A-1 | 30 | 45 | μA |
| | | A-2 | 45 | 60 | μA |
| | | A | 60 | 80 | μA |
| | | B | 80 | 120 | μA |
| | | $V_{AR}=7V$ | | | |